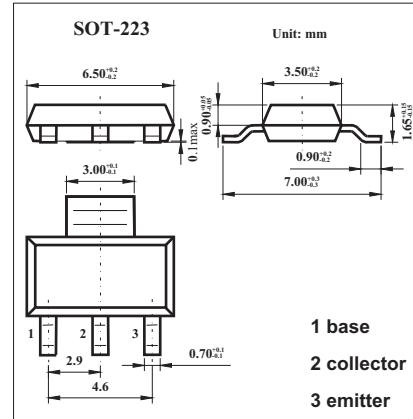


KCP56-16

■ Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
collector-base voltage	V _{CB0}	100	V
collector-emitter voltage	V _{CEO}	80	V
emitter-base voltage	V _{EBO}	5	V
collector current (DC)	I _C	1	A
peak collector current (t _p < 5ms)	I _{CM}	1.5	A
power dissipation	P _D	1.5	W
thermal resistance from junction to ambient	R _{θJA}	94	°C/W
junction temperature	T _j	150	°C
storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA, I _E = 0	100			
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B = 0	80			
Base-emitter breakdown voltage	V _{(BR)EBO}	I _C = 10μA, I _E = 0	5			
Collector cut-off current	I _{CBO}	I _E = 0 A; V _{CB} = 30 V			100	nA
Emitter cut-off current	I _{EBO}	I _C = 0 A; V _{EB} = 5 V			100	nA
DC current gain	h _{FE}	I _C = 5 mA; V _{CE} = 2 V	25			
		I _C = 150 mA; V _{CE} = 2 V	100		250	
		I _C = 500 mA; V _{CE} = 2 V	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500mA; I _B = 50 mA			0.5	V
Transition frequency	f _T	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz		130		MHz